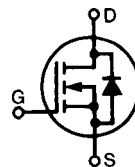


MegaMOS™FET

IXTH 12N90
IXTM 12N90

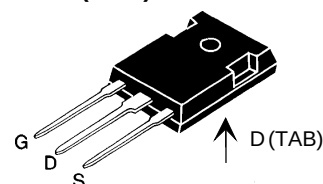
$V_{DSS} = 900\text{ V}$
 $I_{D25} = 12\text{ A}$
 $R_{DS(on)} = 0.90\ \Omega$

N-Channel Enhancement Mode

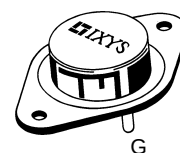


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	900	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	900	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	12	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	48	A
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204 = 18 g, TO-247 = 6 g	
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD (IXTH)



TO-204 AA (IXTM)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Low package inductance ($< 5\text{ nH}$)
 - easy to drive and to protect
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

Advantages

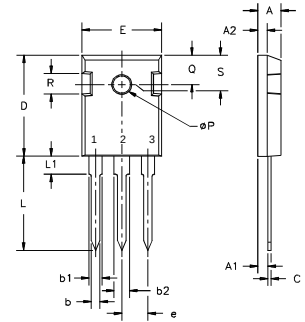
- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$	900		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2		4.5 V
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 100\text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $V_{GS} = 0\text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			250 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5\text{ I}_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			0.90 Ω

Symbol	Test Conditions	Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}$; $I_D = 0.5 \cdot I_{D25}$, pulse test	6	12	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		4500	pF
C_{oss}			315	pF
C_{rss}			65	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$, (External)		20	50 ns
t_r			33	50 ns
$t_{d(off)}$			63	100 ns
t_f			32	50 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 I_{D25}$		145	170 nC
Q_{gs}			30	45 nC
Q_{gd}			55	80 nC
R_{thJC}			0.25	0.42 K/W
R_{thCK}				K/W

Source-Drain Diode		Characteristic Values ($T_j = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			12 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			48 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S$, $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 100\text{ V}$		900	ns

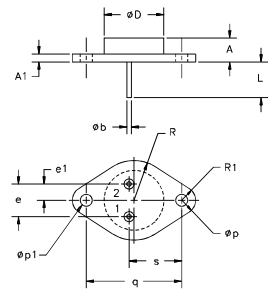
TO-247 AD (IXTH) Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	4.7 5.3	.185 .209
A ₁	2.2 2.54	.087 .102
A ₂	2.2 2.6	.059 .098
b	1.0 1.4	.040 .055
b ₁	1.65 2.13	.065 .084
b ₂	2.87 3.12	.113 .123
C	.4 .8	.016 .031
D	20.80 21.46	.819 .845
E	15.75 16.26	.610 .640
e	5.20 5.72	0.205 0.225
L	19.81 20.32	.780 .800
L1	4.50	.177
ØP	3.55 3.65	.140 .144
Q	5.89 6.40	0.232 0.252
R	4.32 5.49	.170 .216
S	6.15 BSC	.242 BSC

TO-204AA (IXTM) Outline



Pins 1 - Gate 2 - Source
Case - Drain

Dim.	Millimeter Min. Max.	Inches Min. Max.
A	6.4 11.4	.250 .450
A ₁	3.42	.135
Øb	.97 1.09	.038 .043
ØD	22.22	.875
e	10.67 11.17	.420 .440
e1	5.21 5.71	.205 .225
L	7.93	.312
Øp	3.84 4.19	.151 .165
Øp1	3.84 4.19	.151 .165
q	30.15 BSC	1.187 BSC
R	13.33	.525
R1	4.77	.188
s	16.64 17.14	.655 .675

Fig. 1 Output Characteristics

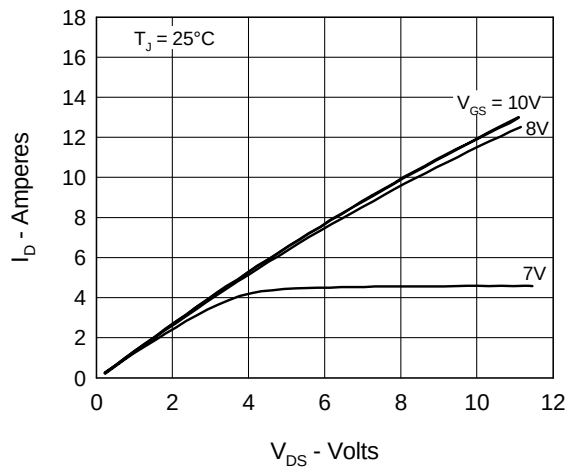


Fig. 2 Input Admittance

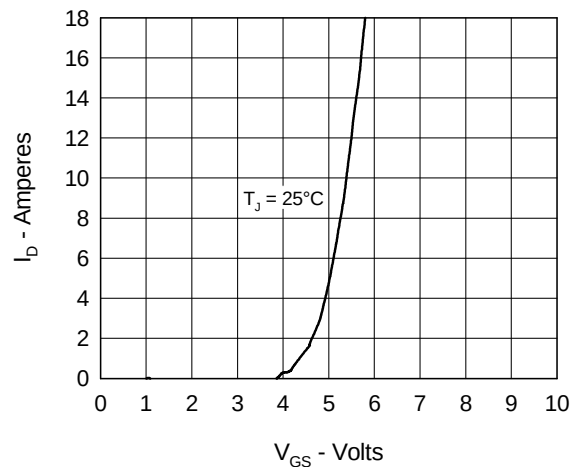


Fig. 3 $R_{DS(on)}$ vs. Drain Current

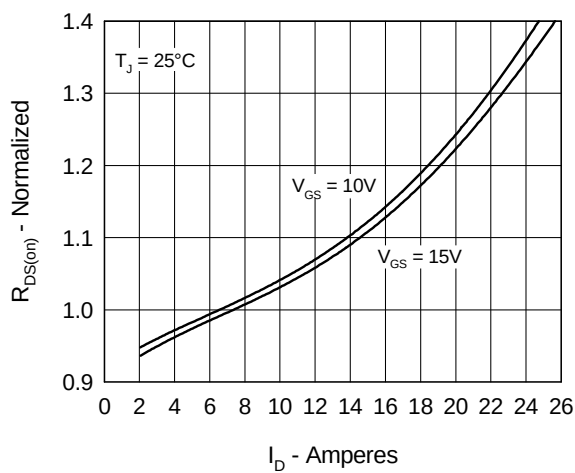


Fig. 4 Temperature Dependence of Drain to Source Resistance

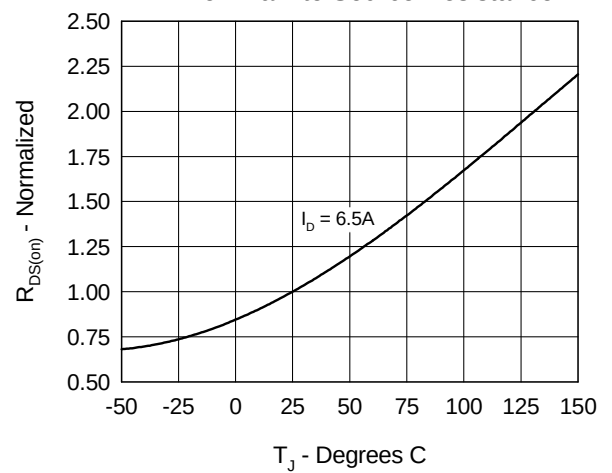


Fig. 5 Drain Current vs. Case Temperature

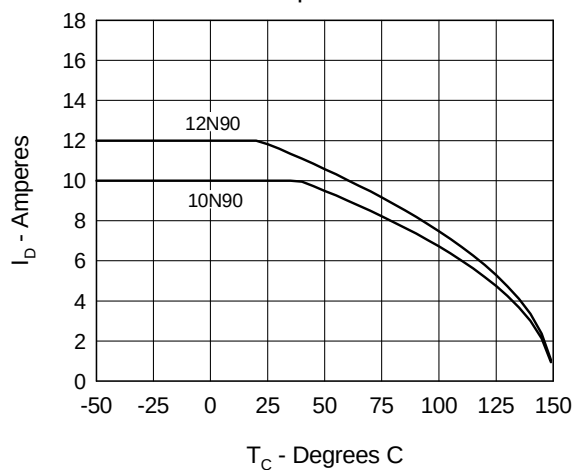


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

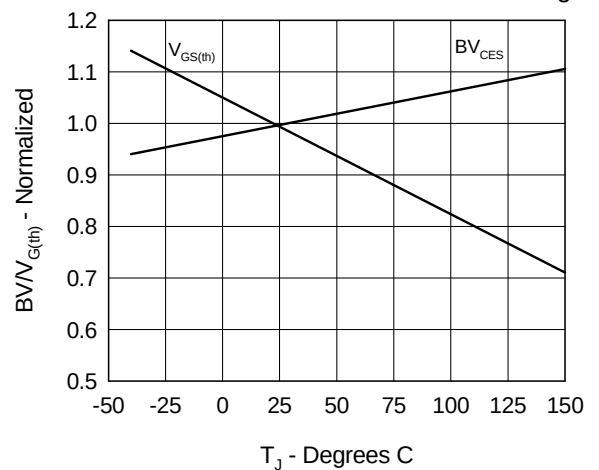


Fig.7 Gate Charge Characteristic Curve

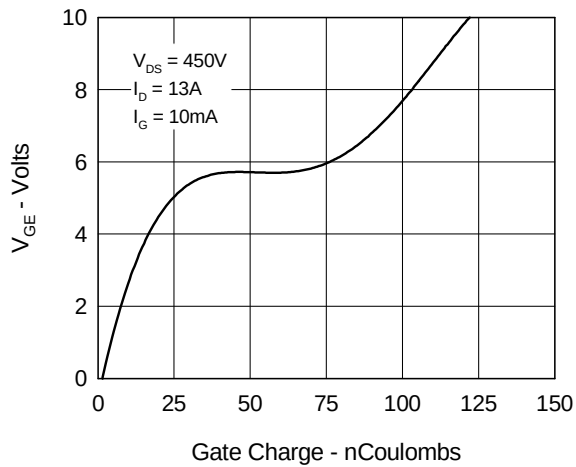


Fig.8 Forward Bias Safe Operating Area

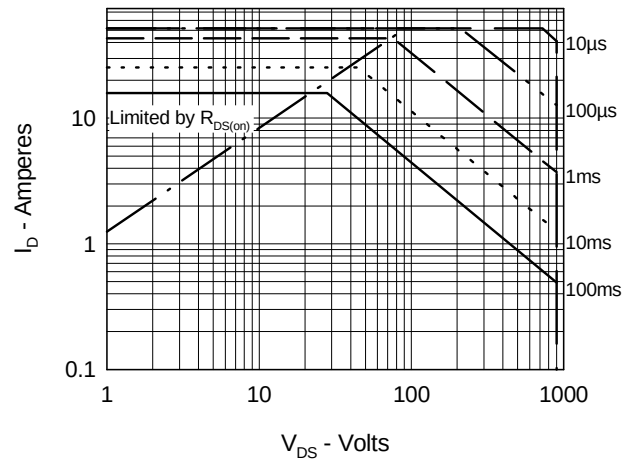


Fig.9 Capacitance Curves

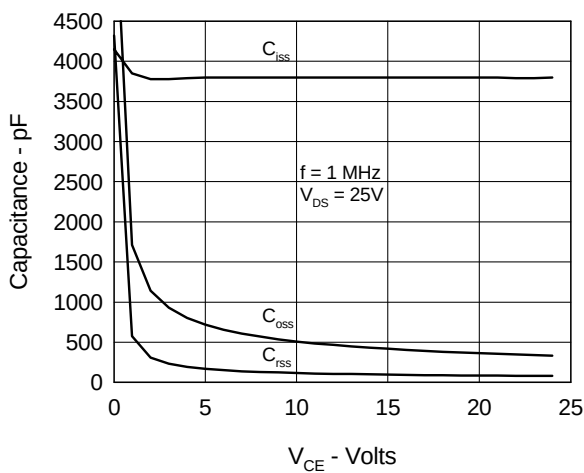


Fig.10 Source Current vs. Source to Drain Voltage

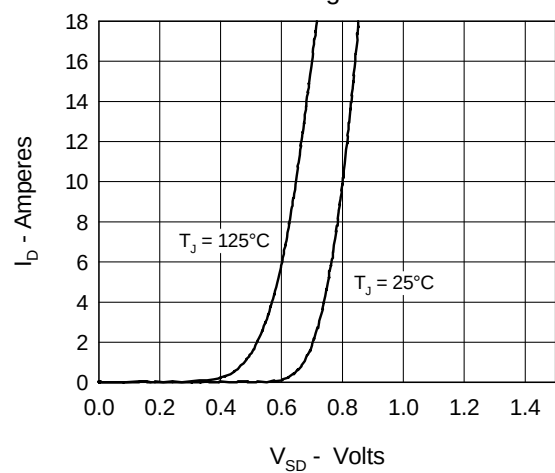


Fig.11 Transient Thermal Impedance

